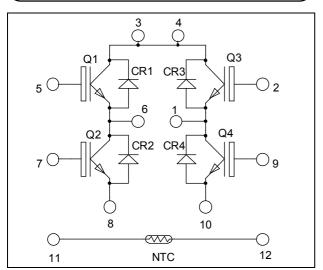
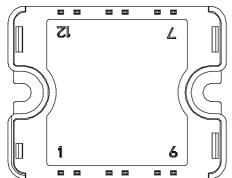


Full - Bridge Trench + Field Stop IGBT3 Power Module





Pins 3/4 must be shorted together

$V_{CES} = 600V$ $I_C = 30A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
 - Symmetrical design
 - Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I.	$\begin{array}{c c} V_{CES} & Collector - Emitter Breakdown Voltage \\ I_C & Continuous Collector Current & T\\ I_{CM} & Pulsed Collector Current & T\\ V_{GE} & Gate - Emitter Voltage \\ P_D & Maximum Power Dissipation & T\\ \end{array}$	$T_C = 25^{\circ}C$	50	
1C		$T_C = 80$ °C	30	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	60	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	90	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150$ °C	60A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 30A$ $T_j = 150^{\circ}C$		1.7		ľ	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 400 \mu A$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				300	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			1600		
Coes	Output Capacitance				110		pF
C_{res}	Reverse Transfer Capacitance				50		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			110		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 30A$			200		
$T_{\rm f}$	Fall Time	$R_G = 10\Omega$			40		i
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$			120		ns
$T_{\rm r}$	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 30A$			250		
$T_{\rm f}$	Fall Time	$R_G = 10\Omega$			60		
Eon	E_{on} Turn-on Switching Energy V_{GE}	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.16		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 300V$	$T_j = 150$ °C		0.3		1113
E_{off}	Turn-off Switching Energy	$I_C = 30A$	$T_j = 25^{\circ}C$		0.7		mJ
Eoff		$R_G = 10\Omega$ $T_j = 150$ °C		1.05		1113	

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V	
I_{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25$ °C			250	μA	
1RM		VR OOOV	$T_j = 150$ °C			500	μΛ	
I_F	DC Forward Current		Tc = 80°C		30		A	
$V_{\rm F}$	Diode Forward Voltage	$I_F = 30A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V	
V F	Diode Forward Voltage		$T_i = 150$ °C		1.5		v	
t_{rr}	Rayarsa Racovary Tima	Recovery Time $ T_{j} = 25^{\circ}C $ $ T_{j} = 150^{\circ}C $	$T_j = 25$ °C		100		ns	
٠rr	Reverse Recovery Time		$T_j = 150$ °C		150		113	
0	O Payanga Pagayany Changa		$I_F = 30A$ $V_R = 300V$	$T_j = 25$ °C		1.5		u.C
Q_{rr}	Reverse Recovery Charge	$di/dt = 1800 \text{ A}/\mu\text{s}$	$T_{\rm j} = 150^{\circ}{\rm C}$		3.1		μC	
Е	В		$T_j = 25$ °C		0.34		mJ	
E_{r}	Reverse Recovery Energy		$T_{\rm j} = 150^{\circ}{\rm C}$		0.75		111J	



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance	IGBT			1.6	°C/	
R_{thJC}		Diode			2.45	W	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range		-40		175		
T_{STG}	Storage Temperature Range			-40		125	°C
T_{C}	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2	·	3	N.m
Wt	Package Weight				80	g	

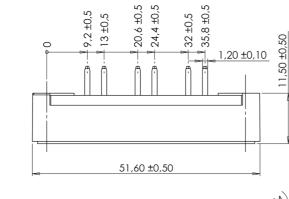
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

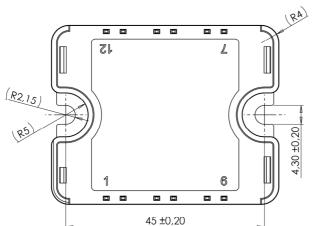
Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

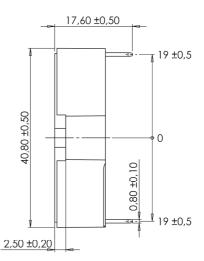
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

SP1 Package outline (dimensions in mm)



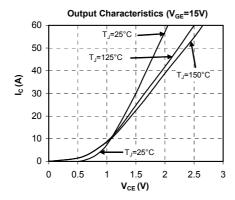


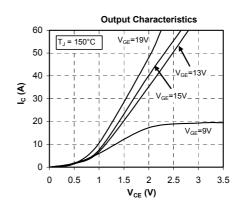


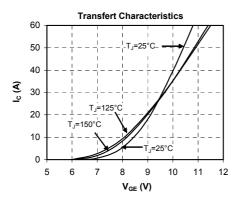
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

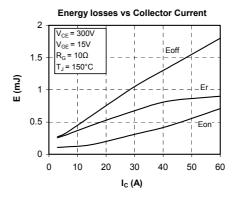


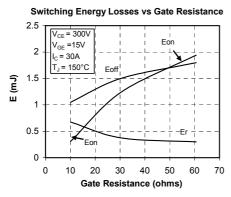
Typical Performance Curve

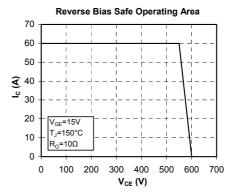


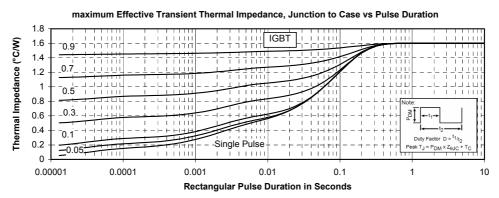




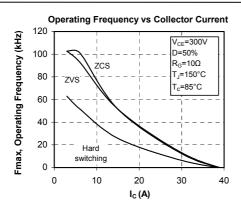


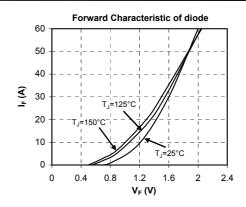


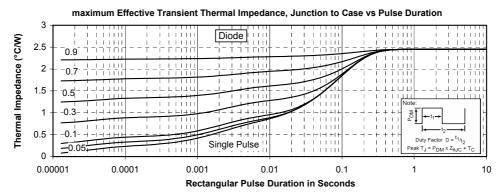














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APTGT30H60T1G - Rev1 October, 2012